

IN THE SPECIFICATION

Please replace the paragraph at page 11, line 32, with the following rewritten paragraph:

41, 44 Wires

Please replace the paragraph at page 17, lines 3-11, with the following rewritten paragraph:

Plural high-frequency semiconductors, that is, MMICs 43 included in the high-frequency package 2 shown in FIG. 1 are accommodated on a bottom surface (the upper surface) ~~[d]41~~ 41 of the cavity 40. The high-frequency semiconductor 43 herein is a generic name of the voltage control oscillator (VCO) 30, the power distributor 32, the multiplier 33, the amplifier 34, the low-noise amplifier (LNA) 38, and the mixer (MIX) 39 included in the high-frequency package 2 shown in FIG. 1.

Please replace the paragraph at page 26, lines 24-32, with the following rewritten paragraph:

The characteristic structures (b) and (c) as key elements of the present invention are explained in detail below with reference to FIG. 9 to FIG. 18. FIG. 9 depicts a simplified internal configuration of the high-frequency package 2 shown in FIG. 3 to FIG. 5. In FIG. 9, the high-frequency package 2 having one of the two cavities 40 shown in FIG. 4 and FIG. 5 is shown. FIG. 10 depicts the high-frequency package shown in ~~FIG. 19~~^[r] FIG. 9 FIG. 9 cut along a line A-A. In FIG. 9, the cover 25 is dismounted.

Please replace the paragraph at page 42, lines 1-13, with the following rewritten paragraph:

~~FIG. 25D[r]25B 25B~~ (the surface A) depicts a part of a via structure on the first-layer surface layer immediately below the high-frequency semiconductor 90. The signal vias 65 and the ground vias 75 are disposed corresponding to the layout of the signal bumps 92a and the ground bumps 92b. FIG. 25C (the surface B) depicts a part of a via structure on the second-layer surface layer immediately below the high-frequency semiconductor 90. FIG. 25D (the surface C) depicts a part of a via structure on the third-layer surface layer immediately below the high-frequency semiconductor 90. The internal-layer signal line 60 is formed on the third-layer surface layer shown as the surface C.